



## PATENT ABSTRACTS OF JAPAN

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WAFER**

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(57) Abstract:

**PURPOSE:** To efficiently work a semiconductor wafer so as to provide it with superior flatness, by arranging the semiconductor wafer so as to face a polishing plate, dipping the surface of the wafer and the polishing plate in polishing liquid, and applying light to the surface to be polished while moving the wafer relatively with respect to the polishing plate.

**CONSTITUTION:** Polishing liquid 7 is injected into a tank 5 and the surface of a semiconductor wafer 2 to be polished and a polishing plate 4 are dipped in the polishing liquid 7. Ultraviolet rays 8 from a light source 3 are applied to the surface of the wafer 2 to be polished, while the wafer 2 and the polishing plate 3 are rotated with the polishing liquid disposed therebetween. Thereby, the surface of the wafer 2 and the polishing liquid 7 are optically or thermally excited uniformly and the reaction between the wafer 2 and the polishing liquid 7 are promoted. In this manner, the wafer 2 can be worked efficiently so as to have superior flatness.

